NSN 5961-00-496-7657

A110a0

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-496-7657 **Inclosure Material:** Metal **Overall Length:** Between 0.450 inches and 0.650 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** Between 0.550 inches and 0.562 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 2.6 forward voltage, peak and 3.5 gate trigger voltage, dc **Current Rating Per Characteristic:** 25.00 amperes forward current, average of standard range and 80.00 milliamperes forward current, total rms preset and 80.00 milliamperes forward current, total rms peak **Power Rating Per Characteristic:** 500.0 milliwatts small-signal input power, common-collector absolute **Maximum Operating Tempurature Per Measurement Point:** 110.0 degrees celsius junction **Special Features:** Internal junction configuration arrangement pnpn **Thread Series Designator:** Unf **Terminal Type And Quantity:** 2 tab, solder lug and 1 threaded stud Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: